

B1  
cont

length larger than the width of source and drain regions, and having a thickness of a gate insulating film formed directly under the entire region of the crosspiece-shaped conductor pattern greater than the thickness of the gate insulating film directly under the main gate electrode.

2. (Twice Amended) An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, wherein a thickness of an insulating film provided on a surface of a first conductivity type semiconductor region positioned at an interface between a first conductivity type body contact region and a second conductivity type source and drain regions is made greater than the thickness of a gate insulating film directly under a gate electrode, said gate electrode being provided on the region except for said body contact region.

3. (Twice Amended) An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, wherein a buried insulating film thicker than the thickness of a gate insulating film directly under a gate electrode is provided on a surface of a first conductivity type semiconductor region positioned at an interface between a first conductivity type body contact region and a second conductivity type source and drain regions, said gate electrode being provided on the region except for said body contact region.

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B<sup>2</sup> 5. (Twice Amended) An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, wherein a gate electrode of a shape of either one of an L-shape or asymmetric T-shape comprised of a trunk-shaped main gate electrode extending in parallel with respect to said semiconductor substrate, and a crosspiece-shaped conductor pattern extending in parallel with respect to said semiconductor substrate and also extending toward the width direction of said main gate electrode is provided and, said trunk-shaped main gate electrode is sandwiched between a source region and a drain region, and at least part of said cross-piece-shaped conductor pattern is also sandwiched between said source region and said drain region, and thereby at least part of said crosspiece-shaped conductor pattern functions as an effective gate electrode.

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Please **add** new claim 9 as follows:

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B<sup>3</sup> 9. (New) An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, wherein a gate electrode of a shape of an asymmetric T-shape comprised of a trunk-shaped main gate electrode and a crosspiece-shaped conductor pattern is provided and a body contact region and one of a source region and drain region are isolated through said crosspiece-shaped conductor pattern, said body contact region being made the same potential as one of said source region and drain region.

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